

Hydrogen interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Thin solid films 2004 / 1/2, p. 53-57 : ill

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn; Kauk, Marit** Materials science and engineering : B 2004 / p. 295-298 : ill

Kas III kvartali majanduskasv valmistas teile pettumuse? : [Äripäeva küsitlusele vastavad Uno Abru, Priit Kivi, Jaak Leimann ja Veikko Maripuu]

Leimann, Jaak; Abru, Uno; Kivi, Priit; Maripuu, Veikko Äripäev 1999 / 7. dets., lk. 31: portr

Point defects interaction with extended defects in the Si-SiO₂ system [Electronic resource]

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM]